

WAFER PRODUCING APPARATUS

ABSTRACT OF THE DISCLOSURE

A wafer producing apparatus for producing an SiC wafer from a single-crystal SiC ingot includes an ingot grinding unit, a laser applying unit that applies a pulsed laser beam having a wavelength that is transmittable through the single-crystal SiC ingot while positioning a focal point of the pulsed laser beam in the single-crystal SiC ingot at a depth corresponding to the thickness of the SiC wafer to be produced from an upper surface of the single-crystal SiC ingot, thereby forming a peel-off layer in the single-crystal SiC ingot, a wafer peeling unit that peels the SiC wafer off the peel-off layer in the single-crystal SiC ingot, and a delivery unit assembly that delivers the single-crystal SiC ingot between the ingot grinding unit, the laser applying unit, and the wafer peeling unit.

Figure 1